# **CNA1012K** (ON1114)

### Photo Interrupter

For contactless SW and object detection

#### Overview

CNA1012K is a photocoupler in which a high efficiency GaAs infrared light emitting diode is used as the light emitting element, and a high sensitivity phototransistor is used as the light detecting element. The two elements are arranged so as to face each other, and objects passing between them are detected.

#### Features

- Highly precise position detection: 0.3 mm
- Wide gap between emitting and detecting elements, suitable for thick plate detection
- Fast response:  $t_r$ ,  $t_f = 6 \ \mu s$  (typ.)
- Small output current variation against change in temperature
- Large output current

#### Absolute Maximum Ratings $T_a = 25\Sigma\Delta\gamma\rho C$

F	Symbol	Rating	Unit		
Input (Light emitting diode)	Power dissipation *1	PD	75	mW	
	Forward current	I <sub>F</sub>	50	mA	
	Reverse voltage V <sub>R</sub> 3		V		
Output (Photo transistor)	Collector-emitter voltage V <sub>CEO</sub> 30		30	v	
	Emitter-collector voltage (Base open)	V <sub>ECO</sub>	5005	V X	
	Collector current	Ic	20	mA	
	Collector power dissipation *2	P <sub>C</sub>	100	mW	
Operating ambient temp	T <sub>opr</sub>	-25 to +85	°C		
Storage temperature	T <sub>stg</sub>	-30 to +100	°C		

Note) \*1: Input power derating ratio is 1.0 mW/°C at  $T_a \ge 25$ °C.

\*2: Output power derating ratio is 1.34 mW/°C at  $T_a \ge 25$ °C.

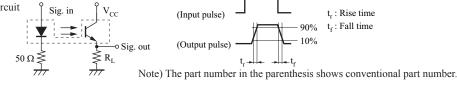
#### Electrical-Optical Characteristics $T_a = 25\Sigma\Delta\gamma\rho C \pm 3\Sigma\Delta\gamma\rho C$

Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Input characteristics	Reverse current	I <sub>R</sub>	$V_R = 3V$			10	μΑ
	Forward voltage	V <sub>F</sub>	$I_{\rm F} = 50  {\rm mA}$		1.2	1.5	V
Output characteristics	Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = 10 V$			200	nA
	Collector-emitter capacitance	C <sub>C</sub>	$V_{CE} = 10 \text{ V}, \text{ f} = 1 \text{ MHz}$		5		pF
Transfer characteristics	Collector current	I <sub>C</sub>	$V_{CE} = 10 \text{ V}, I_F = 20 \text{ mA}$	0.7			mA
	Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_F = 50 \text{ mA}, I_C = 0.1 \text{ mA}$			0.3	V
	Rise time *	t <sub>r</sub>	$V_{\rm CC} = 10 \text{ V}, I_{\rm C} = 1 \text{ mA},$		6.0		μs
	Fall time *	t <sub>f</sub>	$R_L = 100 \Omega$		6.0		μs

Note) 1. Input and output are practiced by electricity.

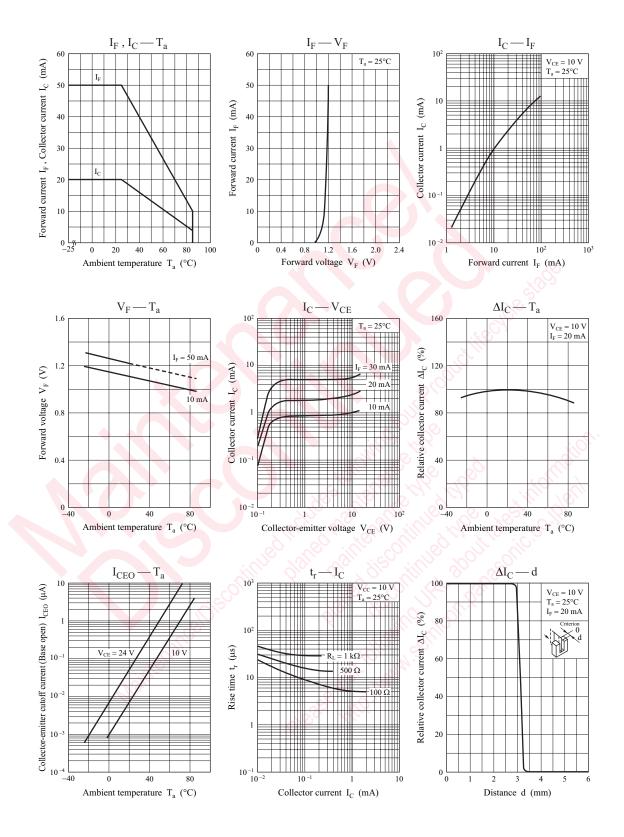
2. This device is designed by disregarding radiation.

3. \*: Switching time measurement circuit <sup>o</sup> Si



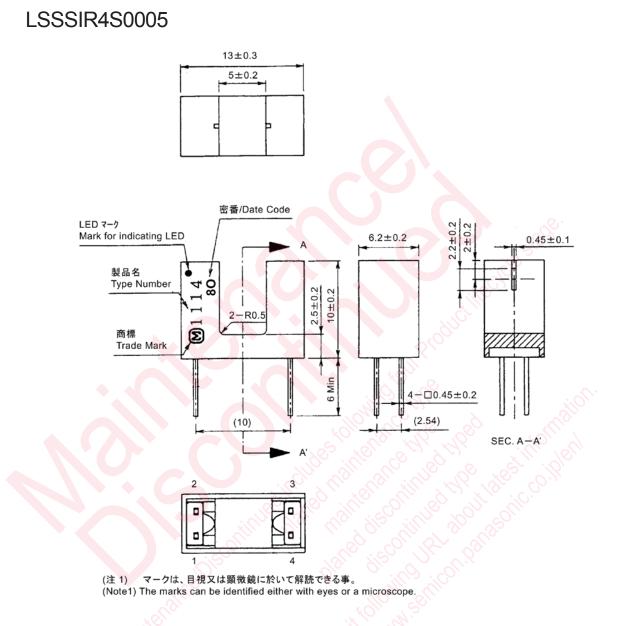
#### CNA1012K

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Package (Unit: mm)



- Pin name
  - 1: Anode
  - 2: Cathode
  - 3: Collector
  - 4: Emitter

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